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Kind regards,

Team Nexperia



# PBSS4580PA

80 V, 5.6 A NPN low  $V_{CEsat}$  (BISS) transistor

Rev. 01 — 15 April 2010

Product data sheet

## 1. Product profile

### 1.1 General description

NPN low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

PNP complement: PBSS5580PA.

### 1.2 Features and benefits

- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

### 1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 1.4 Quick reference data

Table 1. Quick reference data

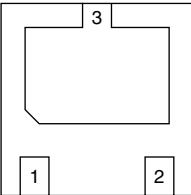
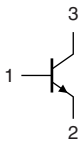
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	80	V
$I_C$	collector current		-	-	5.6	A
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	7	A
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = 5.6$ A; $I_B = 280$ mA	[1] -	40	57	m $\Omega$

[1] Pulse test:  $t_p \leq 300$   $\mu$ s;  $\delta \leq 0.02$ .



## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	base	 <p>Transparent top view</p>	 <p>sym021</p>
2	emitter		
3	collector		

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS4580PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; three terminals; body 2 × 2 × 0.65 mm	SOT1061

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4580PA	AD

## 5. Limiting values

Table 5. Limiting values

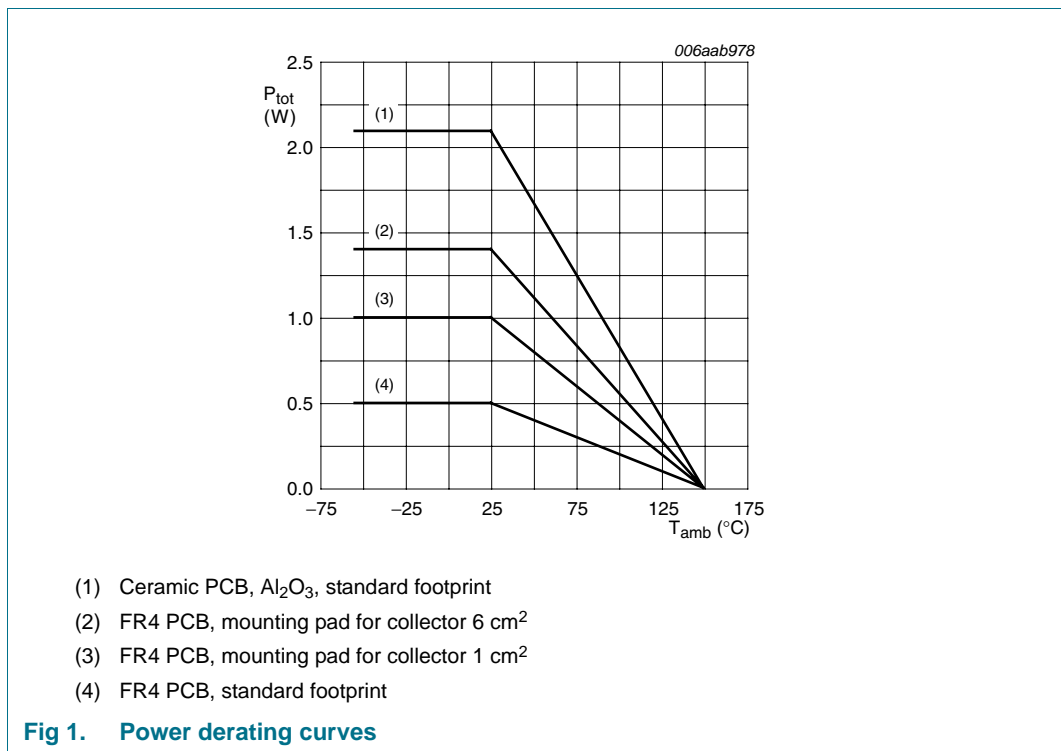
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{CBO}$	collector-base voltage	open emitter	-	80	V	
$V_{CEO}$	collector-emitter voltage	open base	-	80	V	
$V_{EBO}$	emitter-base voltage	open collector	-	6	V	
$I_C$	collector current		-	5.6	A	
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	7	A	
$I_B$	base current		-	600	mA	
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	500	mW
			[2]	-	1	W
			[3]	-	1.4	W
			[4]	-	2.1	W

**Table 5. Limiting values ...continued**  
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
$T_j$	junction temperature		-	150	°C
$T_{amb}$	ambient temperature		-55	+150	°C
$T_{stg}$	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

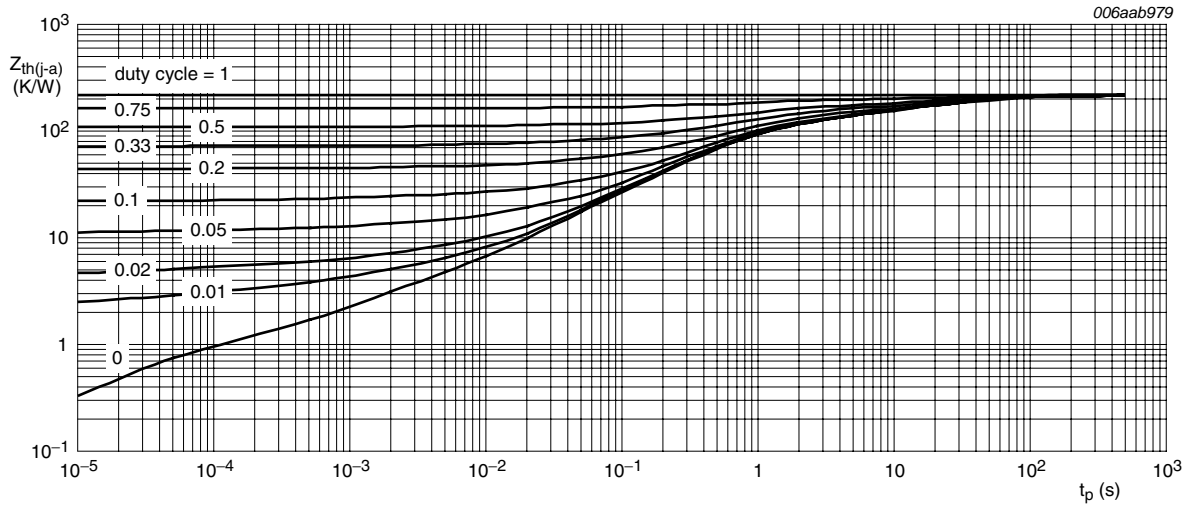


## 6. Thermal characteristics

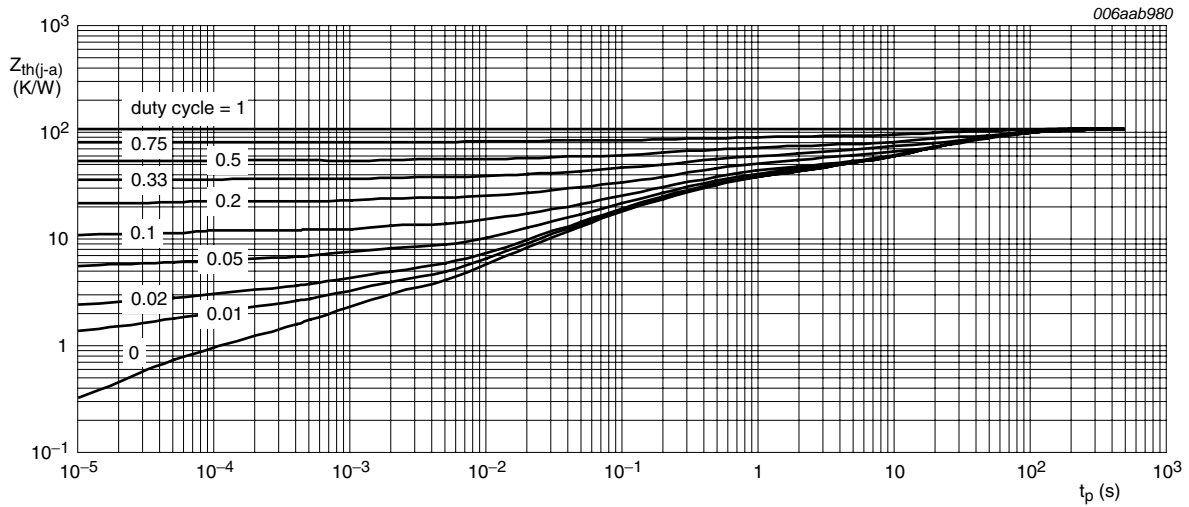
**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W
			[2]	-	-	125	K/W
			[3]	-	-	90	K/W
			[4]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



**Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

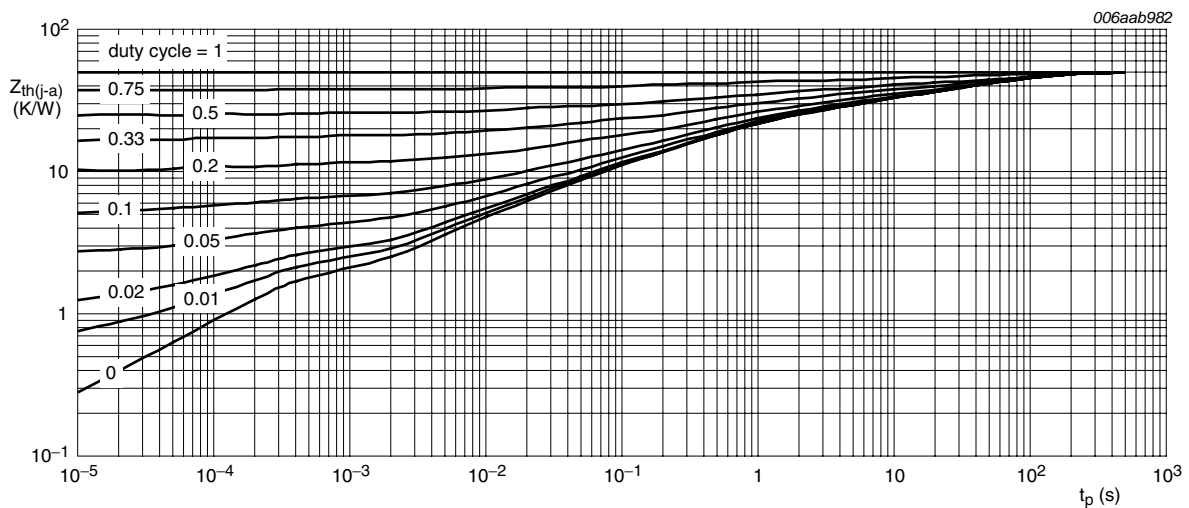


**Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**



FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>

**Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

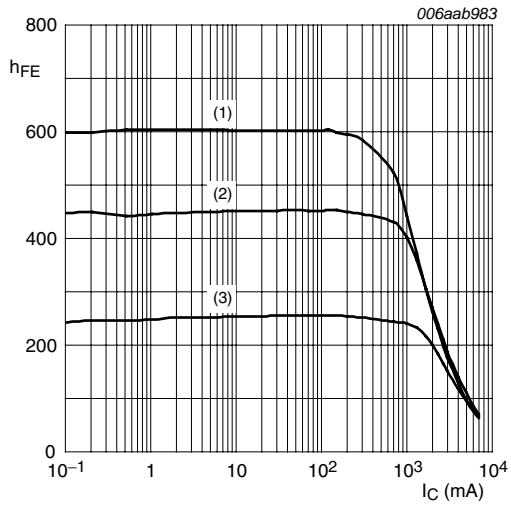
**Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

## 7. Characteristics

**Table 7. Characteristics**
 $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

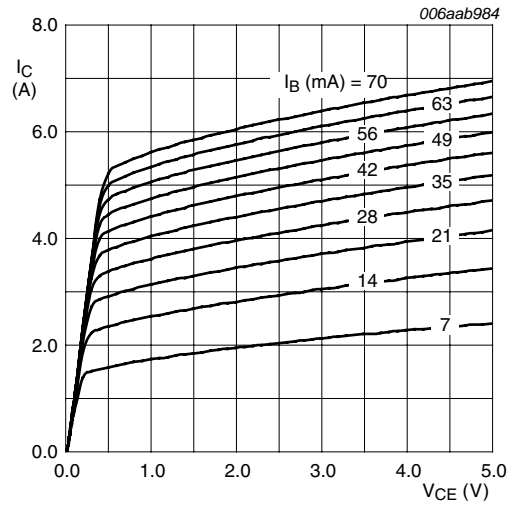
Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 64\text{ V}; I_E = 0\text{ A}$	-	-	100	nA	
		$V_{CB} = 64\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	$\mu\text{A}$	
$I_{CES}$	collector-emitter cut-off current	$V_{CE} = 64\text{ V}; V_{BE} = 0\text{ V}$	-	-	100	nA	
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	100	nA	
$h_{FE}$	DC current gain	$V_{CE} = 2\text{ V}$	[1]				
		$I_C = 0.5\text{ A}$	270	425	-		
		$I_C = 1\text{ A}$	240	375	-		
		$I_C = 2\text{ A}$	150	245	-		
		$I_C = 6\text{ A}$	45	75	-		
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 0.5\text{ A}; I_B = 50\text{ mA}$	[1]	-	25	35	mV
		$I_C = 1\text{ A}; I_B = 50\text{ mA}$	[1]	-	50	70	mV
		$I_C = 1\text{ A}; I_B = 10\text{ mA}$	[1]	-	85	120	mV
		$I_C = 2\text{ A}; I_B = 20\text{ mA}$	[1]	-	150	220	mV
		$I_C = 3\text{ A}; I_B = 30\text{ mA}$	[1]	-	265	360	mV
		$I_C = 4\text{ A}; I_B = 400\text{ mA}$	[1]	-	155	210	mV
		$I_C = 5.6\text{ A}; I_B = 280\text{ mA}$	[1]	-	230	320	mV
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = 5.6\text{ A}; I_B = 280\text{ mA}$	[1]	-	40	57	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 10\text{ mA}$	[1]	-	0.74	0.9	V
		$I_C = 5.6\text{ A}; I_B = 280\text{ mA}$	[1]	-	1	1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 2\text{ A}$	[1]	-	0.76	0.9	V
$t_d$	delay time	$V_{CC} = 9\text{ V}; I_C = 2\text{ A}; I_{Bon} = 0.1\text{ A}; I_{Boff} = -0.1\text{ A}$	-	21	-	ns	
$t_r$	rise time		-	162	-	ns	
$t_{on}$	turn-on time		-	183	-	ns	
$t_s$	storage time		-	720	-	ns	
$t_f$	fall time		-	205	-	ns	
$t_{off}$	turn-off time		-	925	-	ns	
$f_T$	transition frequency	$V_{CE} = 10\text{ V}; I_C = 100\text{ mA}; f = 100\text{ MHz}$	95	155	-	MHz	
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	-	20	25	pF	

[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .



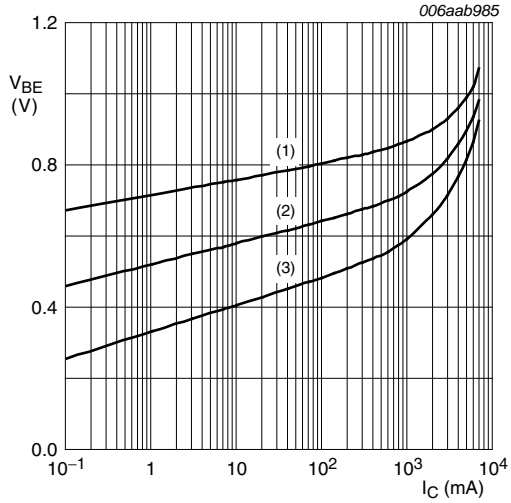
$V_{CE} = 2\text{ V}$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig 6. DC current gain as a function of collector current; typical values**



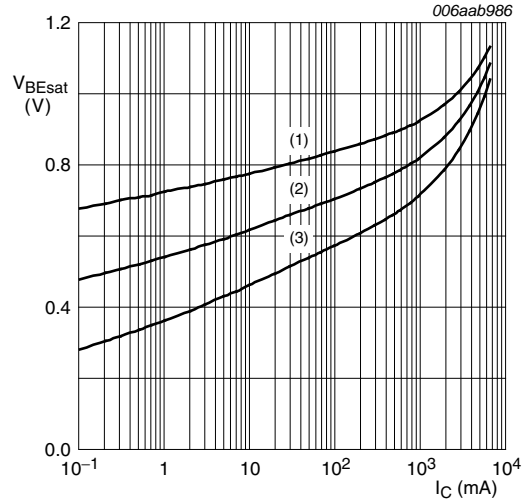
$T_{amb} = 25\text{ }^\circ\text{C}$

**Fig 7. Collector current as a function of collector-emitter voltage; typical values**



$V_{CE} = 2\text{ V}$   
 (1)  $T_{amb} = -55\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

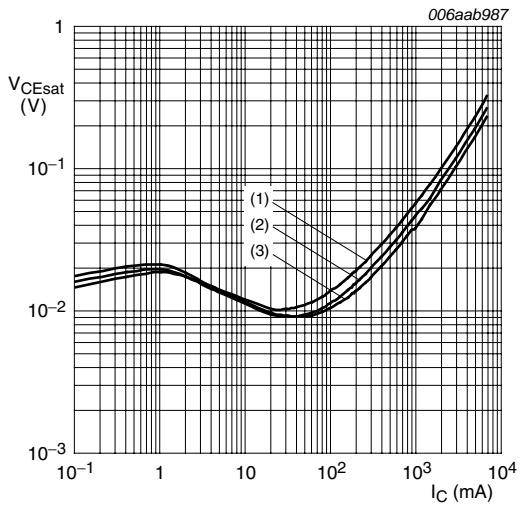
**Fig 8. Base-emitter voltage as a function of collector current; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = -55\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

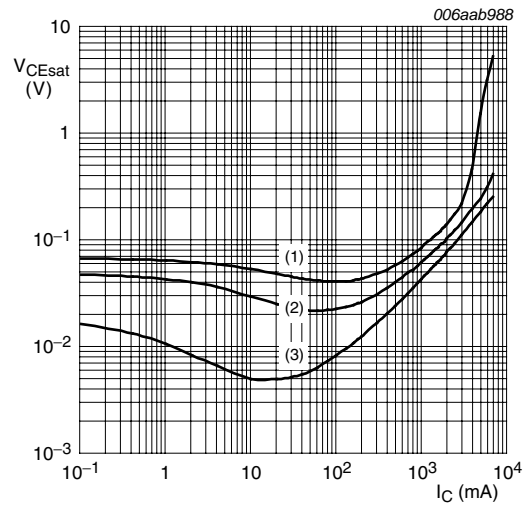
**Fig 9. Base-emitter saturation voltage as a function of collector current; typical values**





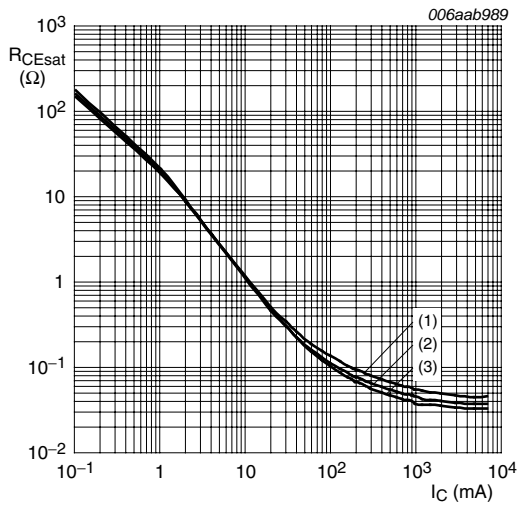
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

**Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values**



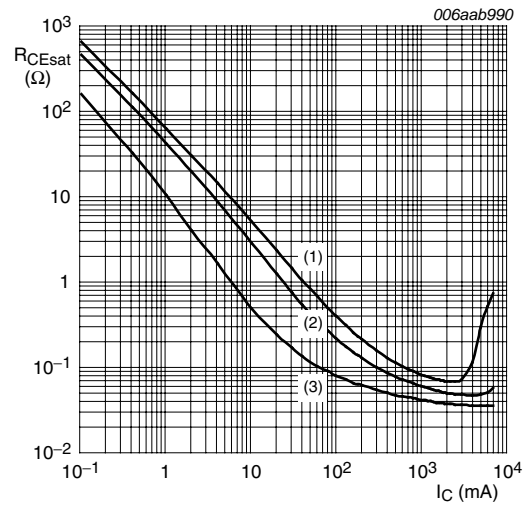
$T_{amb} = 25\text{ °C}$   
 (1)  $I_C/I_B = 100$   
 (2)  $I_C/I_B = 50$   
 (3)  $I_C/I_B = 10$

**Fig 11. Collector-emitter saturation voltage as a function of collector current; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

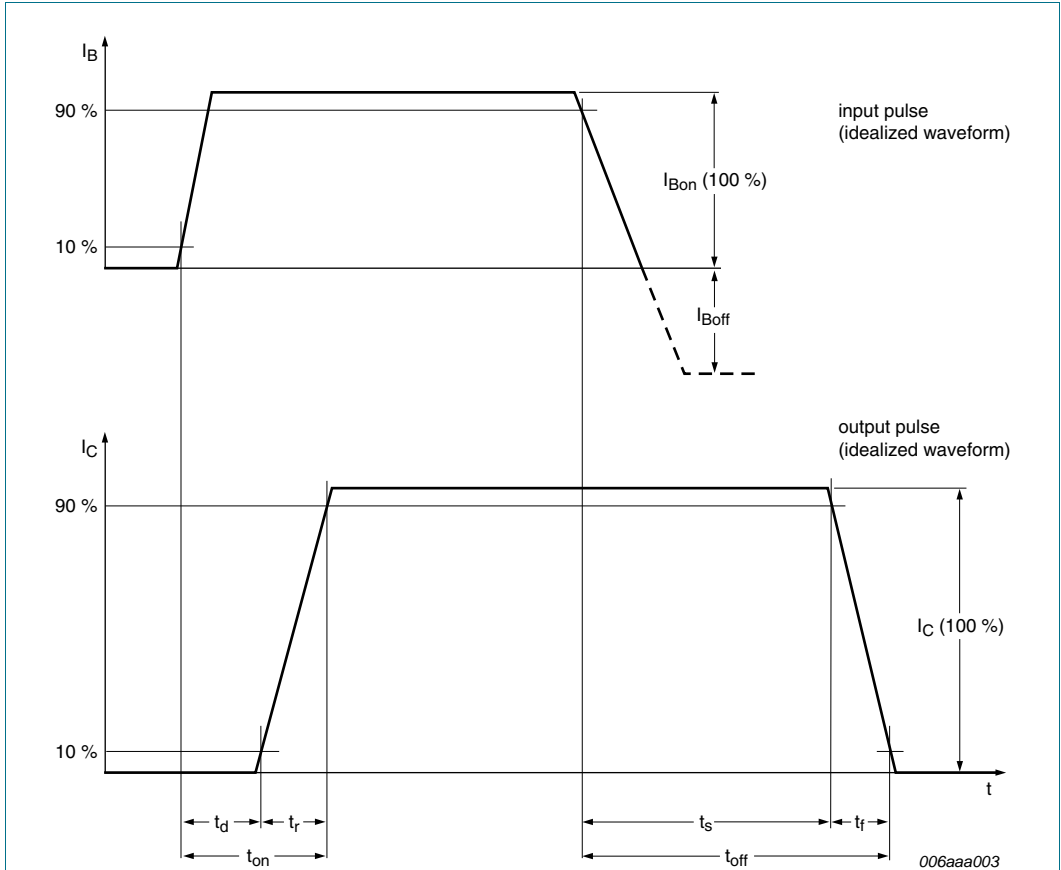
**Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values**



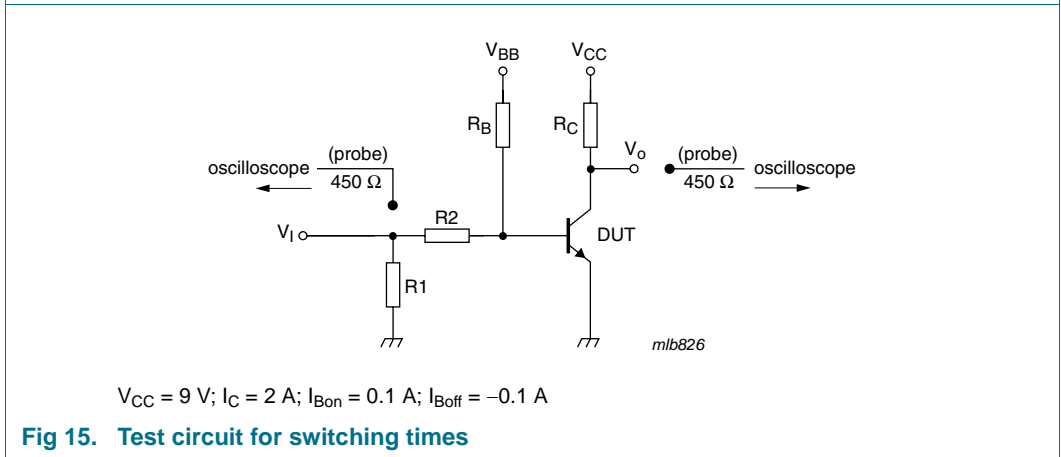
$T_{amb} = 25\text{ °C}$   
 (1)  $I_C/I_B = 100$   
 (2)  $I_C/I_B = 50$   
 (3)  $I_C/I_B = 10$

**Fig 13. Collector-emitter saturation resistance as a function of collector current; typical values**

**8. Test information**



**Fig 14. BISS transistor switching time definition**



$V_{CC} = 9\text{ V}$ ;  $I_C = 2\text{ A}$ ;  $I_{Bon} = 0.1\text{ A}$ ;  $I_{Boff} = -0.1\text{ A}$

**Fig 15. Test circuit for switching times**

## 9. Package outline



## 10. Packing information

**Table 8. Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

Type number	Package	Description	Packing quantity
PBSS4580PA	SOT1061	4 mm pitch, 8 mm tape and reel	3000
			-115

[1] For further information and the availability of packing methods, see [Section 14](#).

**11. Soldering**



## 12. Revision history

**Table 9.** Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4580PA_1	20100415	Product data sheet	-	-

## 13. Legal information

### 13.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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